

ABSTRACT

The present invention is a semiconductor device having the semiconductor element 1 obtained by cutting a semiconductor wafer with the electrode pad 2 formed 5 on one side along the scribe line, the semiconductor element protective layer 7 on the semiconductor element 1 which has the opening 7(1) on the pad 2, the stress cushioning layer 3 on the layer 7 which has the opening 3(1) on the pad 2, the lead wire portion 4 reaching the layer 3 from the electrode pad 2 via the 10 openings 7(1) and 3(1), the external electrodes 6 on the lead wire portion 4, and the conductor protective layer 5 on the layer 3 and the layer 7, the layer 3, and the conductor protective layer 5 form the 15 respective end faces on the end surface 1(1) of the semiconductor element 1 inside the scribe line and expose the range from the end face of the end surface 1(1) to the inside of the scribe line.